

- Advanced Process Technology
- Surface Mount
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching
- Lead-Free

### Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

### Absolute Maximum Ratings

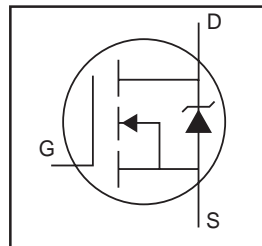
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}^{\text{⑤}}$	61	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}^{\text{⑤}}$	39	
$I_{DM}$	Pulsed Drain Current ①⑤	240	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	89	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$E_{AS}$	Single Pulse Avalanche Energy②⑤	220	mJ
$I_{AR}$	Avalanche Current①	35	A
$E_{AR}$	Repetitive Avalanche Energy①	8.9	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

### Thermal Resistance

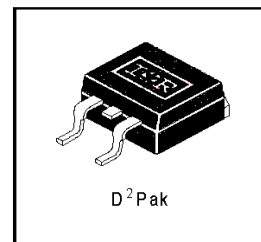
	Parameter	Typ.	Max.	Units
$R_{qJC}$	Junction-to-Case	---	1.4	°C/W
$R_{qJA}$	Junction-to-Ambient ( PCB Mounted, steady-state)**	---	40	

PD-95589  
**IRL3102SPbF**

HEXFET® Power MOSFET



$V_{DSS} = 20\text{V}$
$R_{DS(on)} = 0.013\Omega$
$I_D = 61\text{A}$



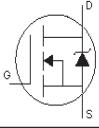
# IRL3102SPbF

International  
IR Rectifier

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0\text{V}$ , $I_D = 250\mu\text{A}$
$DV_{(BR)DSS}/DT_J$	Breakdown Voltage Temp. Coefficient	—	0.016	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.015	$\Omega$	$V_{GS} = 4.5\text{V}$ , $I_D = 37\text{A}$ ④
		—	—	0.013		$V_{GS} = 7.0\text{V}$ , $I_D = 37\text{A}$ ④
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$
$g_{fs}$	Forward Transconductance	36	—	—	S	$V_{DS} = 16\text{V}$ , $I_D = 35\text{A}$ ⑤
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu\text{A}$	$V_{DS} = 20\text{V}$ , $V_{GS} = 0\text{V}$
		—	—	250		$V_{DS} = 10\text{V}$ , $V_{GS} = 0\text{V}$ , $T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 10\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -10\text{V}$
$Q_g$	Total Gate Charge	—	—	58	nC	$I_D = 35\text{A}$
$Q_{gs}$	Gate-to-Source Charge	—	—	14		$V_{DS} = 16\text{V}$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	21		$V_{GS} = 4.5\text{V}$ , See Fig. 6 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = 10\text{V}$
$t_r$	Rise Time	—	130	—		$I_D = 35\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	80	—		$R_G = 9.0\text{m}\Omega$ , $V_{GS} = 4.5\text{V}$
$t_f$	Fall Time	—	110	—		$R_D = 0.28\text{m}\Omega$ ④⑤
$L_S$	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
$C_{iss}$	Input Capacitance	—	2500	—	pF	$V_{GS} = 0\text{V}$
$C_{oss}$	Output Capacitance	—	1000	—		$V_{DS} = 15\text{V}$
$C_{rss}$	Reverse Transfer Capacitance	—	360	—		$f = 1.0\text{MHz}$ , See Fig. 5

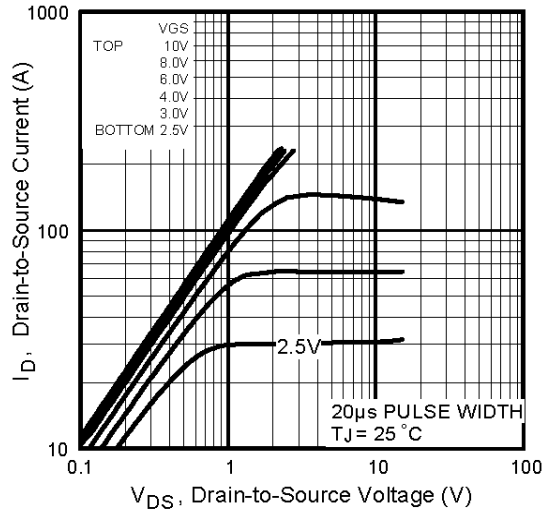
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	61	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①⑤	—	—	240		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}$ , $I_S = 37\text{A}$ , $V_{GS} = 0\text{V}$ ④
$t_{rr}$	Reverse Recovery Time	—	59	88	ns	$T_J = 25^\circ\text{C}$ , $I_F = 35\text{A}$
$Q_{rr}$	Reverse Recovery Charge	—	110	160	nC	$di/dt = 100\text{A}/\mu\text{s}$ ④⑤
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

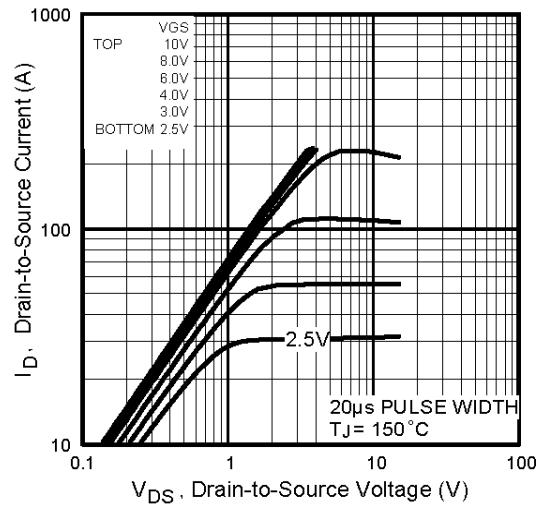
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.36\text{mH}$ ,  $R_G = 25\text{m}\Omega$ ,  $I_{AS} = 35\text{A}$ .
- ③  $I_{SD} \leq 35\text{A}$ ,  $di/dt \leq 100\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤ Uses IRL3102 data and test conditions

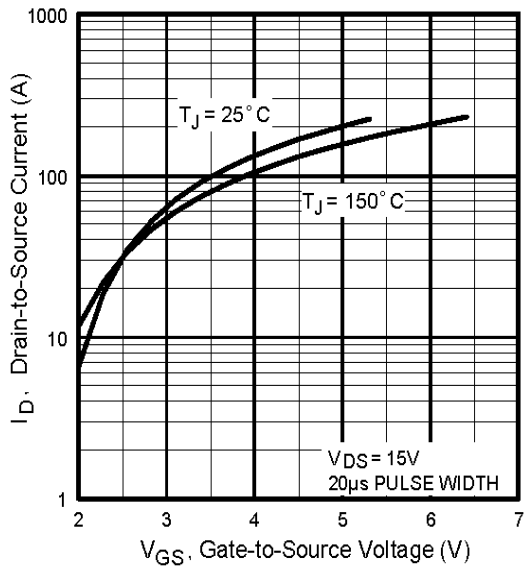
\*\* When mounted on FR-4 board using minimum recommended footprint.  
For recommended footprint and soldering techniques refer to application note #AN-994.



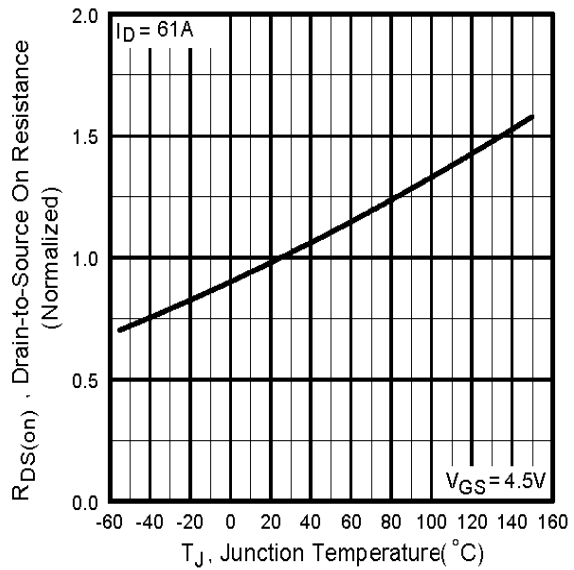
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



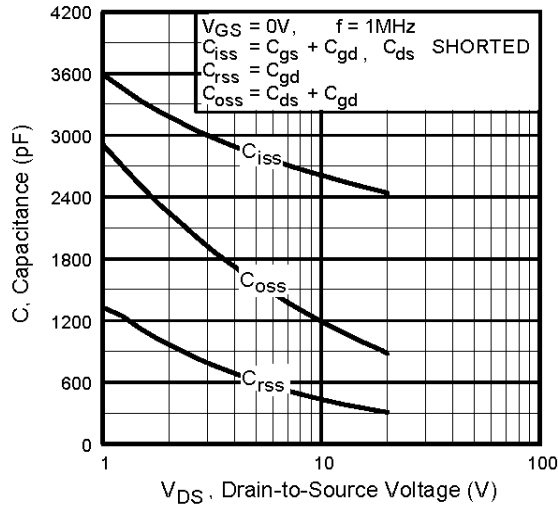
**Fig 3.** Typical Transfer Characteristics



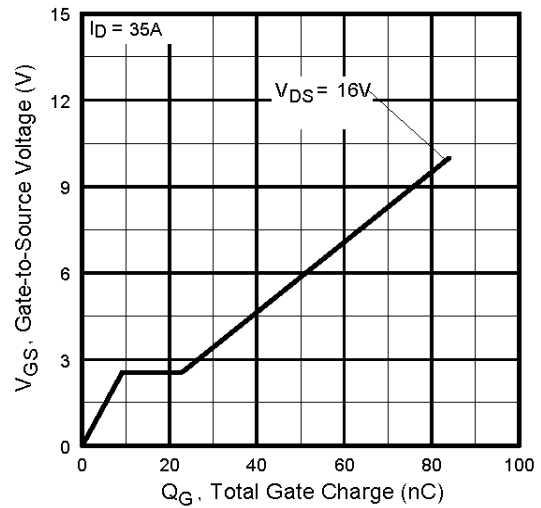
**Fig 4.** Normalized On-Resistance Vs. Temperature

# IRL3102SPbF

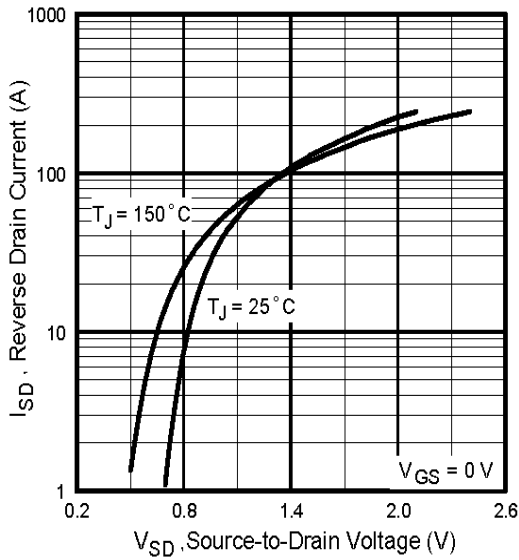
International  
**IR** Rectifier



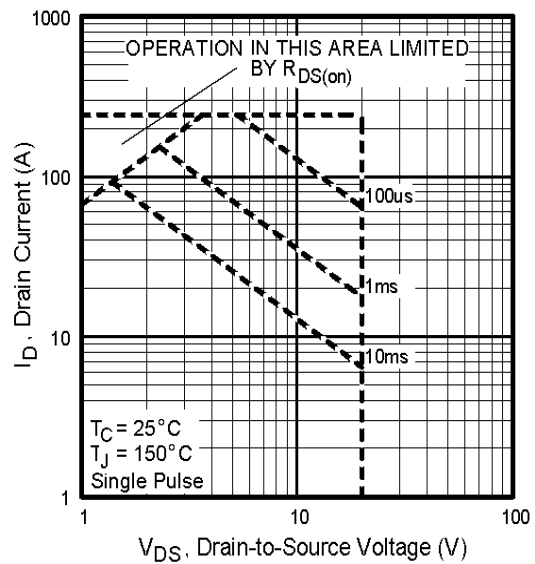
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



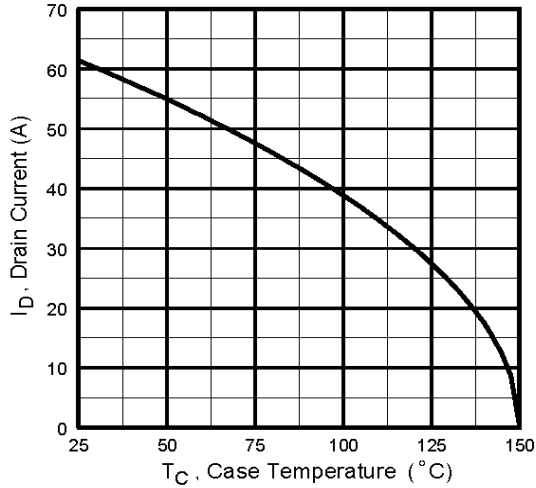
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



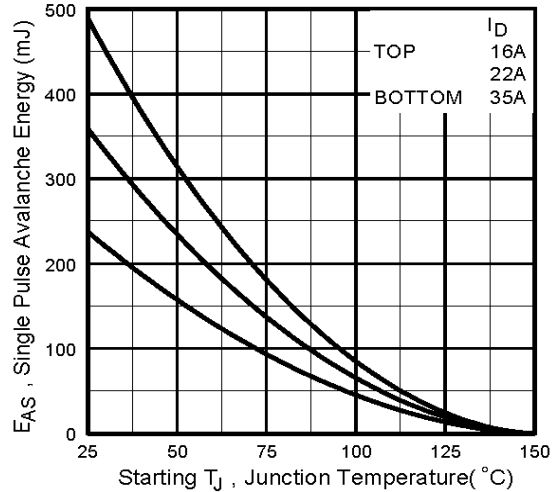
**Fig 7.** Typical Source-Drain Diode Forward Voltage



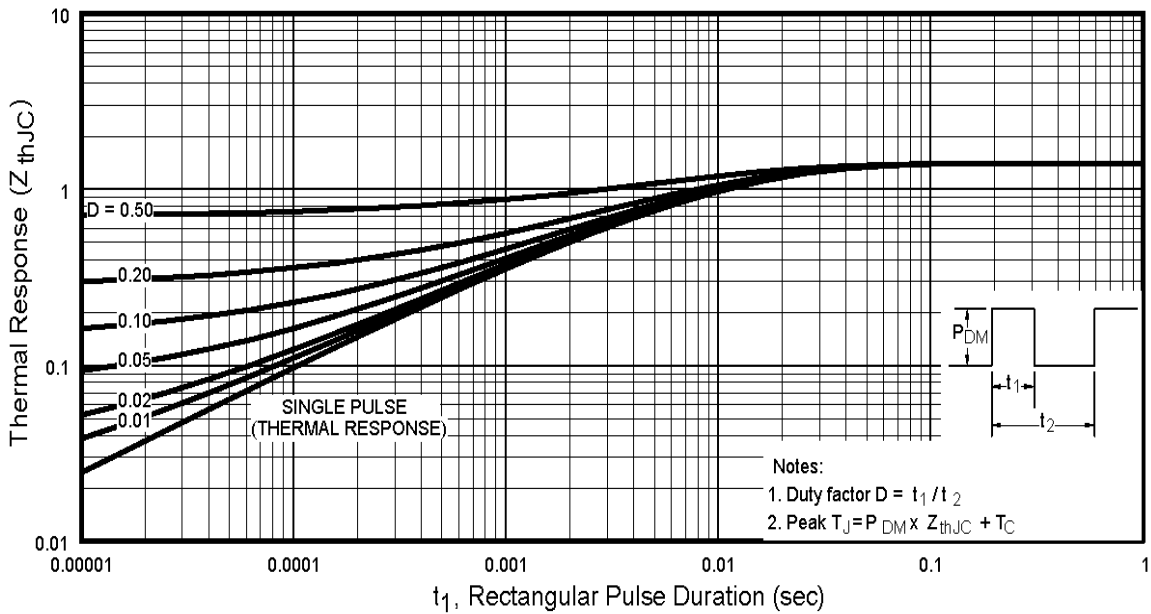
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current Vs. Case Temperature

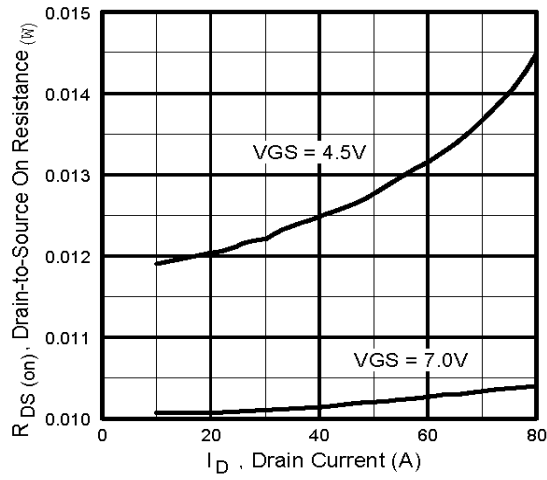


**Fig 10.** Maximum Avalanche Energy Vs. Drain Current

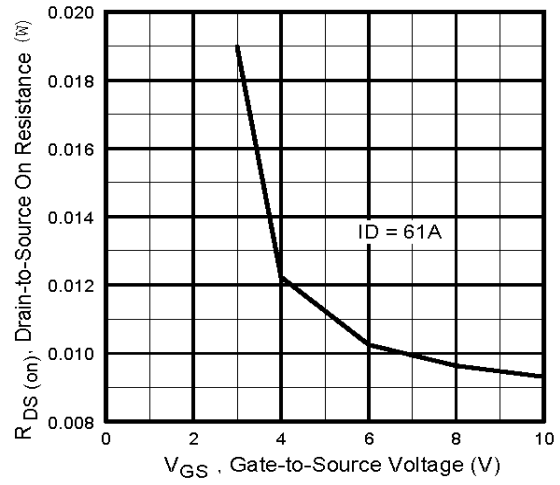


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRL3102SPbF



**Fig 12.** On-Resistance Vs. Drain Current

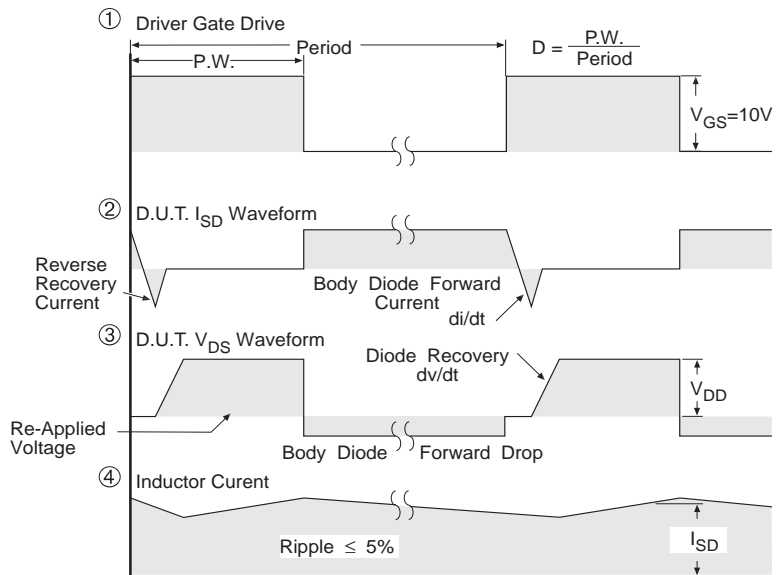


**Fig 13.** On-Resistance Vs. Gate Voltage

**Peak Diode Recovery dv/dt Test Circuit**



\* Reverse Polarity for P-Channel  
\*\* Use P-Channel Driver for P-Channel Measurements



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

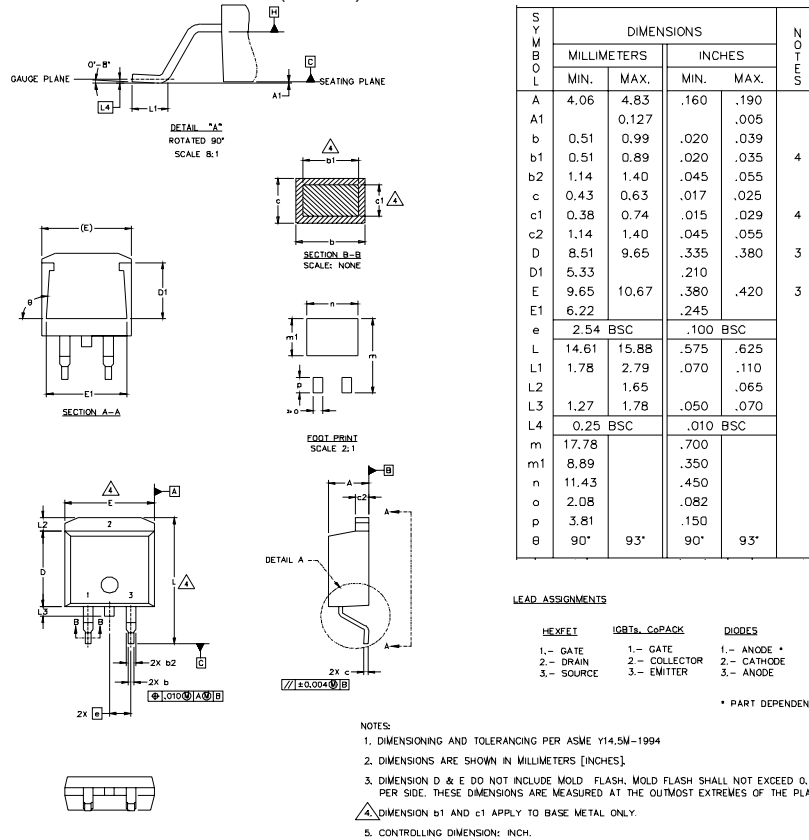
**Fig 14 For N Channel HEXFETS**

# IRL3102SPbF

International  
**IR** Rectifier

## D<sup>2</sup>Pak Package Outline

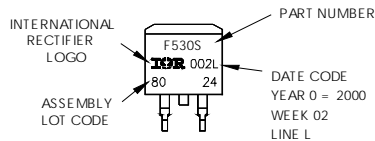
Dimensions are shown in millimeters (inches)



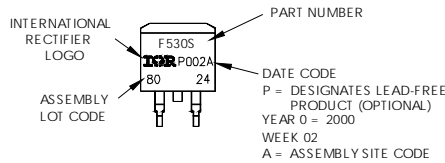
## D<sup>2</sup>Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024 ASSEMBLED ON WW 02, 2000 IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead-Free"



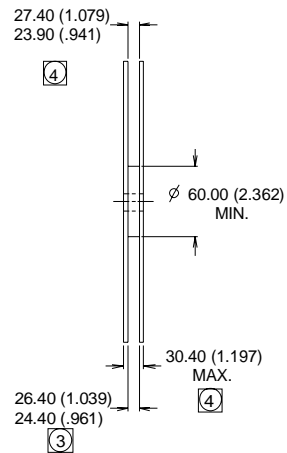
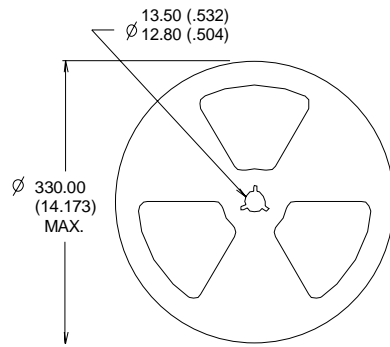
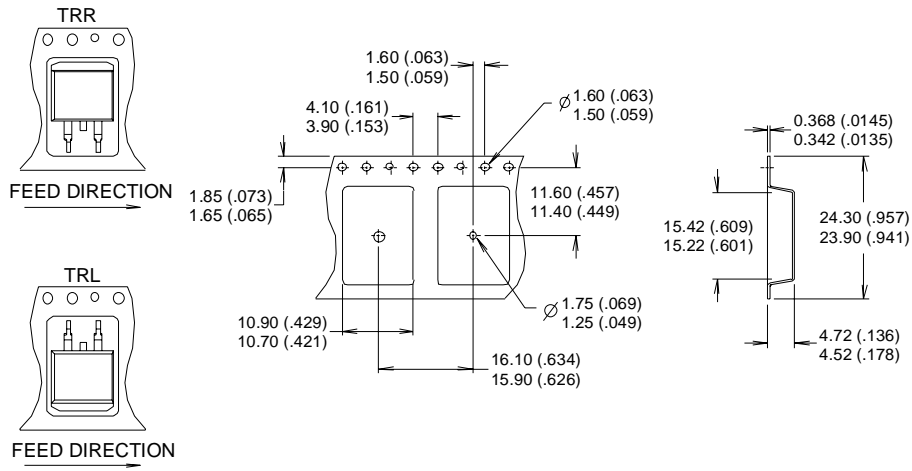
**OR**





## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - ③ DIMENSION MEASURED @ HUB.
  - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.